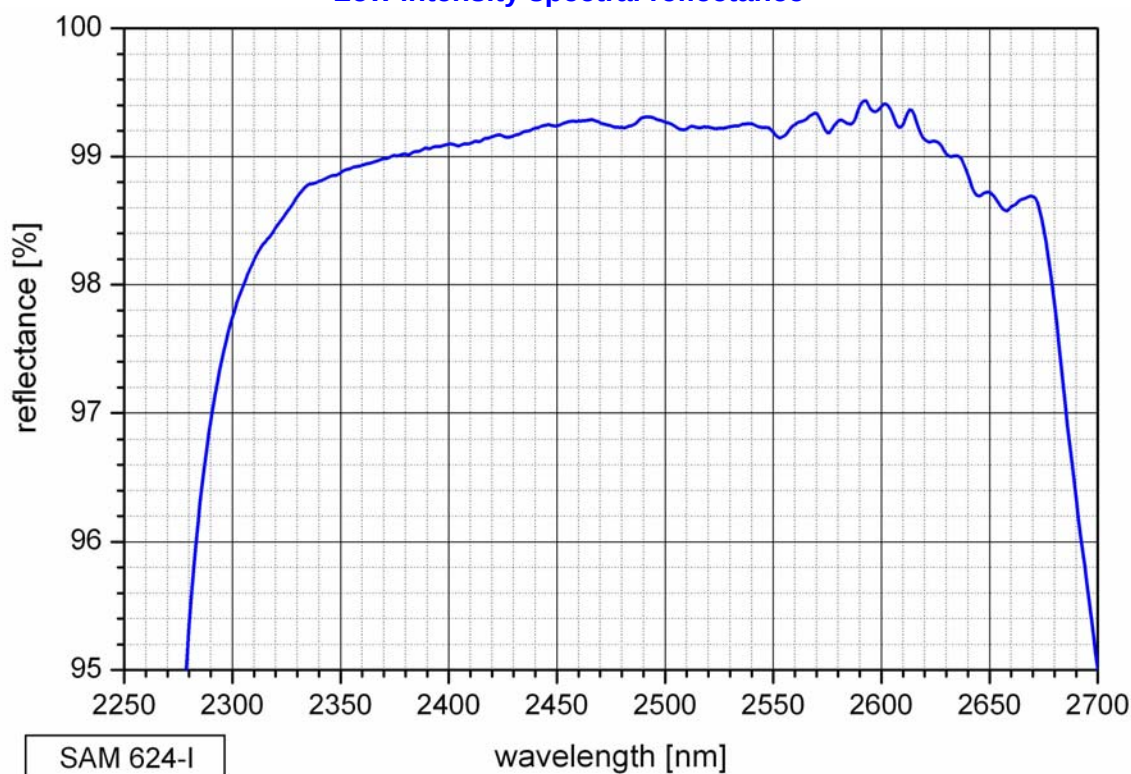


SAM™ data sheet SAM-2400-1-x-500fs, $\lambda = 2400$ nm

Laser wavelength	$\lambda = 2400$ nm
High reflection band (R > 98%)	$\lambda = 2300 \dots 2650$ nm
Absorbance	$A_0 = 1$ %
Modulation depth	$\Delta R = 0.6$ %
Non-saturable loss	$A_{ns} = 0.4$ %
Saturation fluence	$\Phi_{sat} = 90 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 500$ fs
Damage threshold	$800 \text{ MW}/\text{cm}^2$
Chip area	4mm x 4mm; other dimensions on request
Chip thickness	620 μm
Protection	the SAM is protected with a dielectric AR layer
Reverse design	the absorber layer is illuminated through the 620 μm thick GaAs wafer
Mounting of SAM-2400-1-x-500fs denotes the type of mounting as follows:	
$x = 0$	unmounted
$x = 12.7$ g	glued on a copper heat sink with 12.7 mm diameter
$x = 25.4$ g	glued on a copper heat sink with 25.4 mm diameter
$x = 12.7$ s	soldered on a copper heat sink with 12.7 mm diameter
$x = 25.4$ s	soldered on a copper heat sink with 25.4 mm diameter
$x = 25.0$ w	soldered on a water cooled copper heat sink with 25.0 mm diameter

Low intensity spectral reflectance



Reverse design of the SAM-2400-1-x-500fs

